

N-Channel 40-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

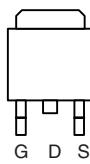
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
40	0.0053 at $V_{GS} = 10$ V	110	95

FEATURES

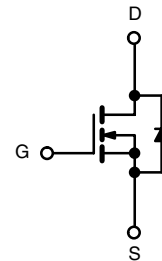
- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- High Threshold Voltage at High Temperature


RoHS
COMPLIANT

TO-263



Top View

Ordering Information: SUM110N04-05H-E3 (Lead (Pb)-free)


N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	110
		$T_C = 125$ °C	70
Pulsed Drain Current	I_{DM}	300	A
Avalanche Current	I_{AR}	50	
Repetitive Avalanche Energy ^a	E_{AR}	125	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	150 ^b
		$T_A = 25$ °C ^c	3.75
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case	R_{thJC}	1	

Notes:

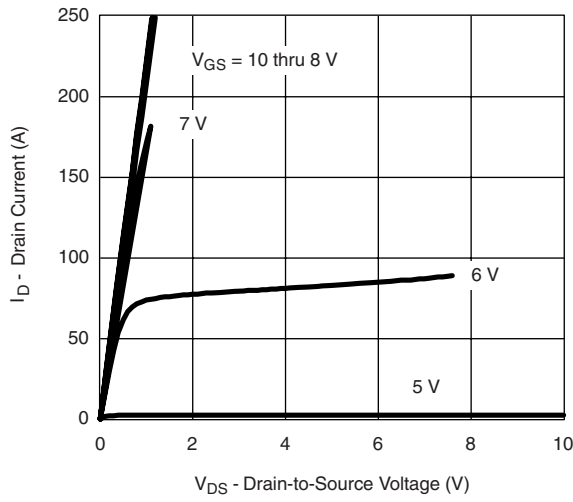
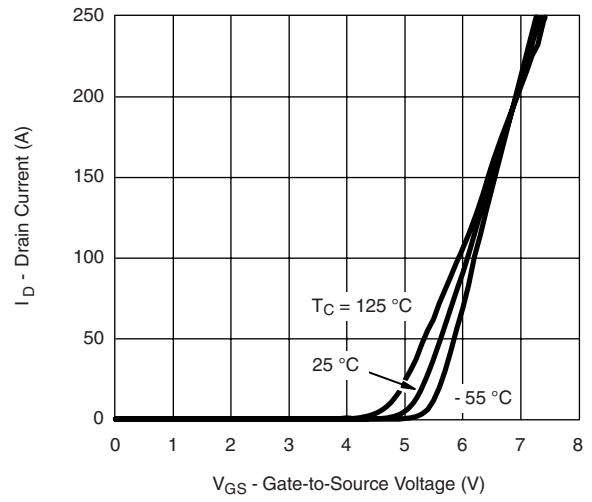
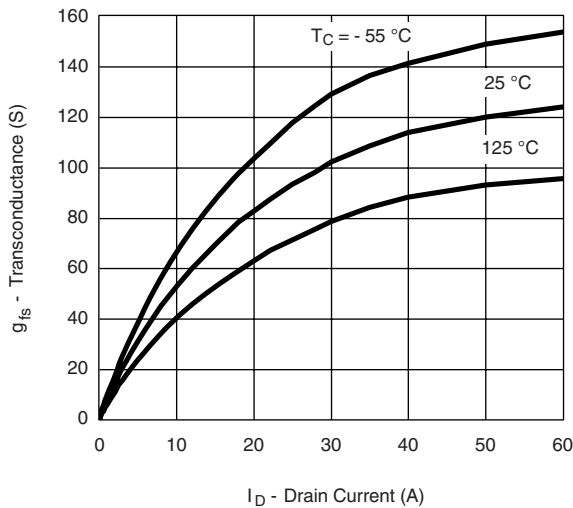
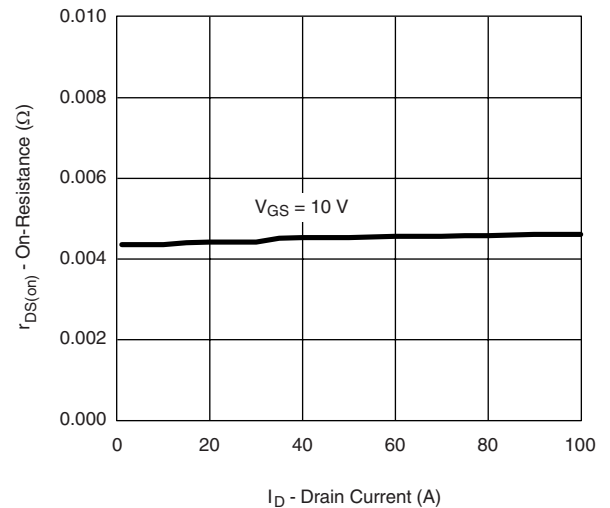
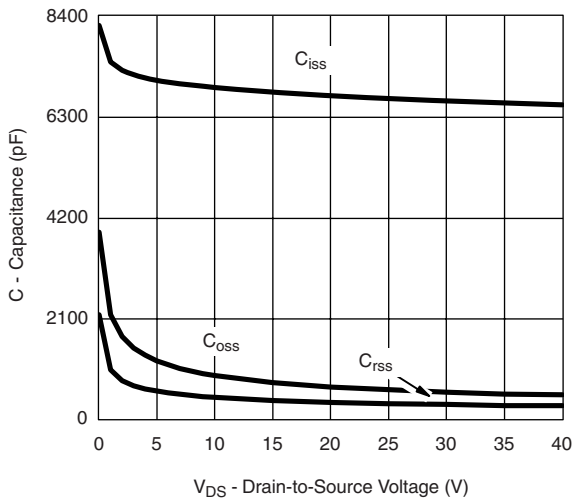
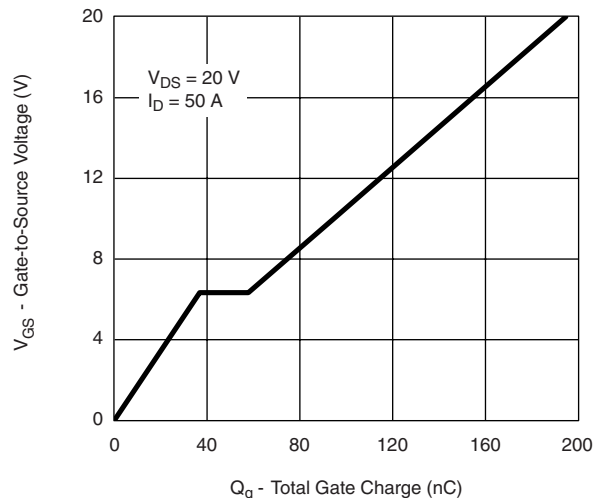
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.4	3.8	5.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.0044	0.0053	Ω
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.008	
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.0106	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$	20	50		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6700		pF
Output Capacitance	C_{oss}			600		
Reverse Transfer Capacitance	C_{rss}			320		
Total Gate Charge ^c	Q_g	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		95		nC
Gate-Source Charge ^c	Q_{gs}			37		
Gate-Drain Charge ^c	Q_{gd}			21		
Gate Resistance	R_g	$f = 1.0\text{ MHz}$		1.7		Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 0.4\text{ }\Omega$ $I_D \cong 50\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		20	30	ns
Rise Time ^c	t_r			95	145	
Turn-Off Delay Time ^c	$t_{d(off)}$			50	75	
Fall Time ^c	t_f			12	20	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}$ ^b						
Continuous Current	I_S				100	A
Pulsed Current	I_{SM}				300	
Forward Voltage ^a	V_{SD}	$I_F = 30\text{ A}, V_{GS} = 0\text{ V}$		0.90	1.50	V
Reverse Recovery Time	t_{rr}	$I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		40	60	ns

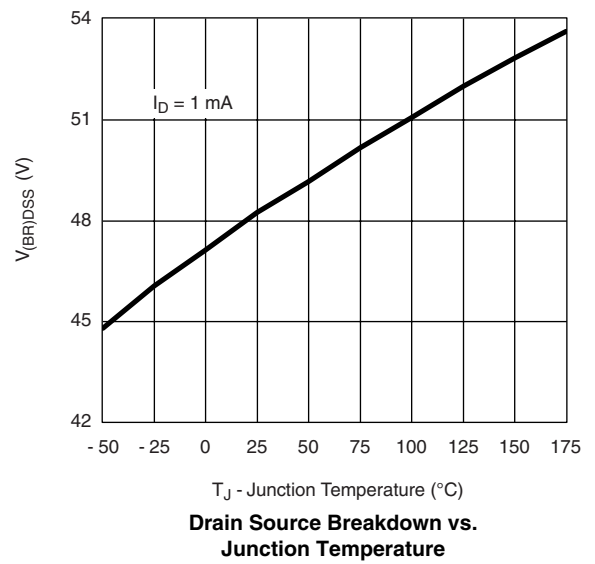
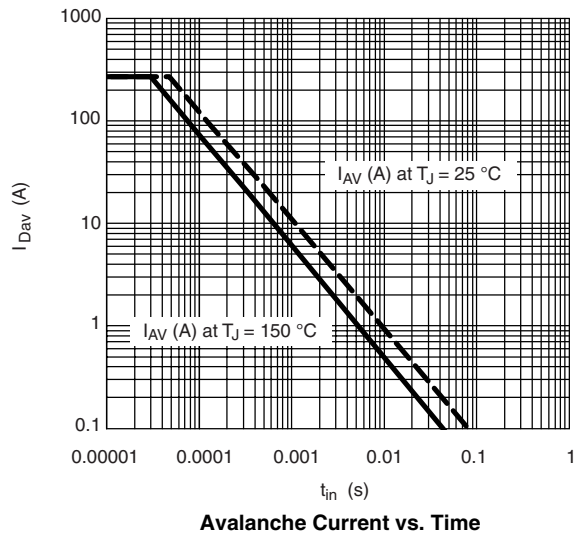
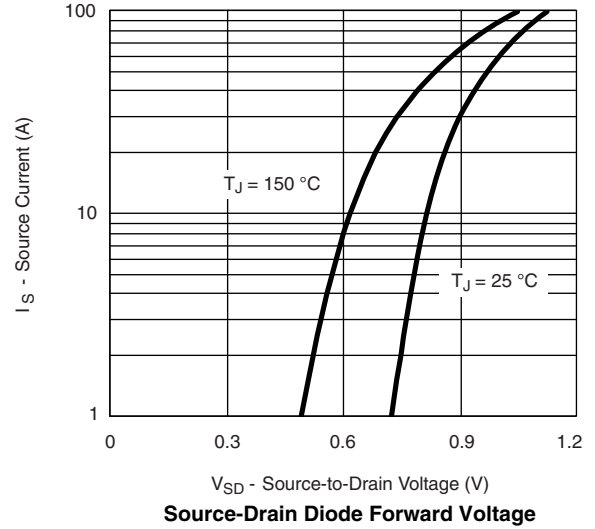
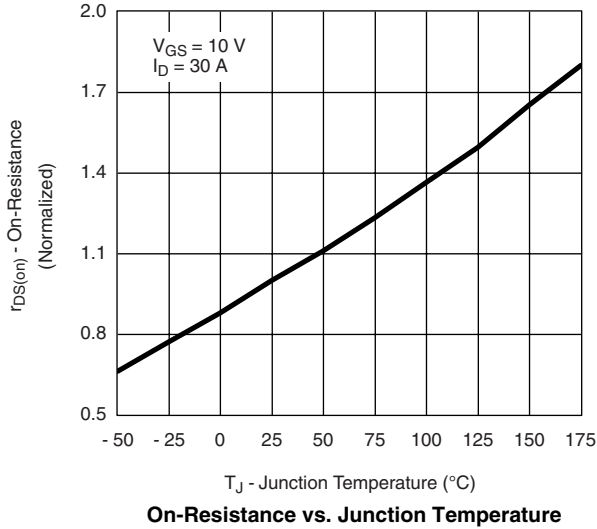
Notes:

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

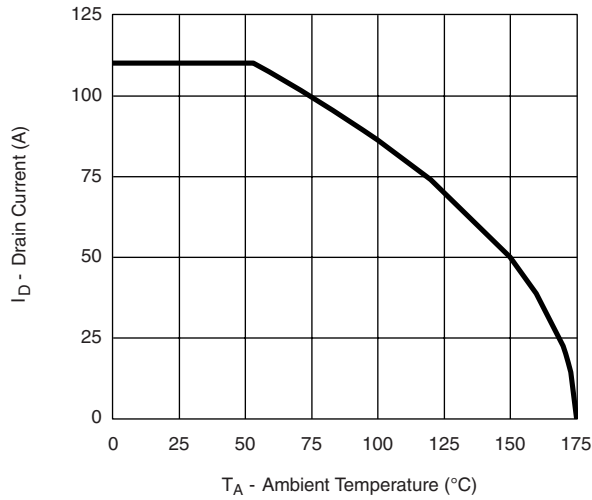
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

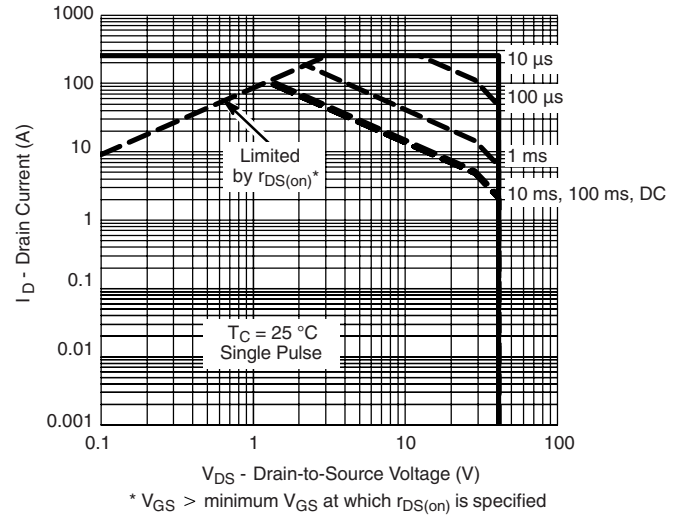
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



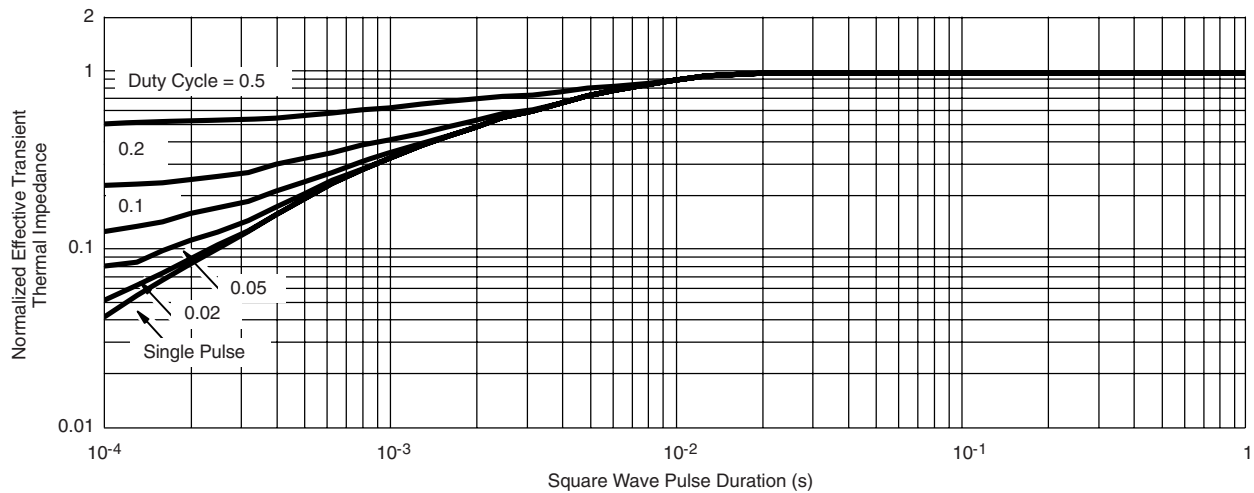
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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